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(54) **DISPLAY SUBSTRATE AND PREPARATION METHOD THEREOF, AND DISPLAY APPARATUS**

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ABSTRACT

The present disclosure provides a display substrate and a preparation method thereof, and a display apparatus. The display substrate includes a circuit layer disposed on a base substrate, an emitting structure layer and a photoelectric structure layer disposed on a side of the circuit layer away from the base substrate, the circuit layer includes at least one impurity absorption layer and at least one transistor, the transistor includes an active layer, and at least one insulation layer is provided between the impurity absorption layer and the active layer; an atomic ratio of a silicon element to a nitrogen element in the impurity absorption layer is 1:5 to 1:35.

